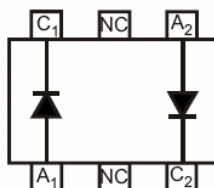


SCHOTTKY DIODE

FEATURES

Surface mount schottky barrier diode arrays

Marking: KAV



Maximum Ratings @ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	833	$^{\circ}\text{C}/\text{W}$
Storage temperature	T_{STG}	-65-125	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	30		V
Reverse voltage leakage current	I_R	$V_R=25\text{V}$		2	μA
Forward voltage	V_F	$I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=30\text{mA}$ $I_F=100\text{mA}$		320 400 500 1000	mV
Total capacitance	C_T	$V_R=1\text{V}, f=1\text{MHz}$		10	pF
Reverse recovery time	t_{rr}	$I_F=10\text{mA}, I_R=10\text{mA}\sim 1\text{mA}$ $R_L=100\Omega$		5	nS

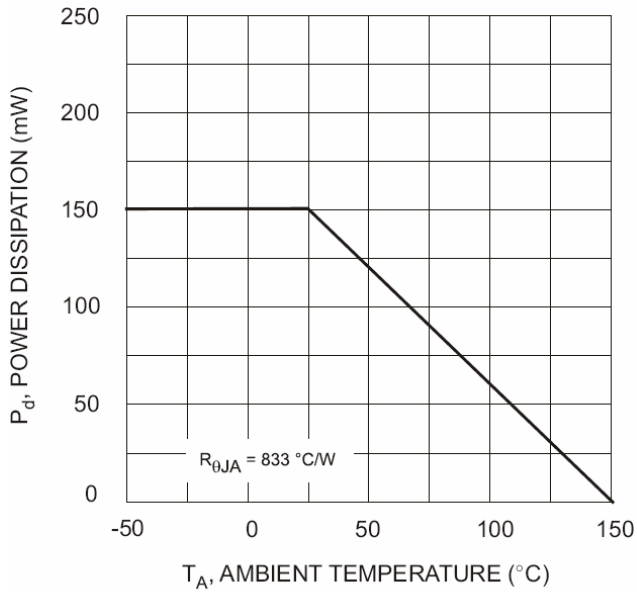
Typical Characteristics


Fig. 1, Derating Curve - Total

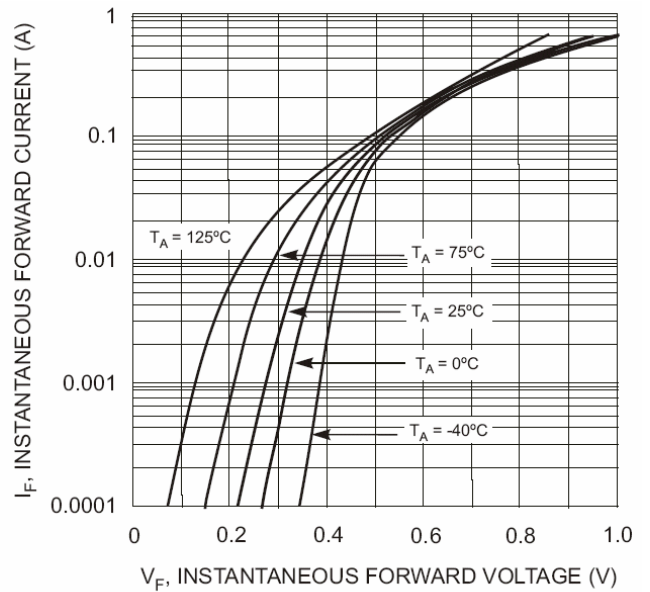


Fig. 2 Forward Characteristics

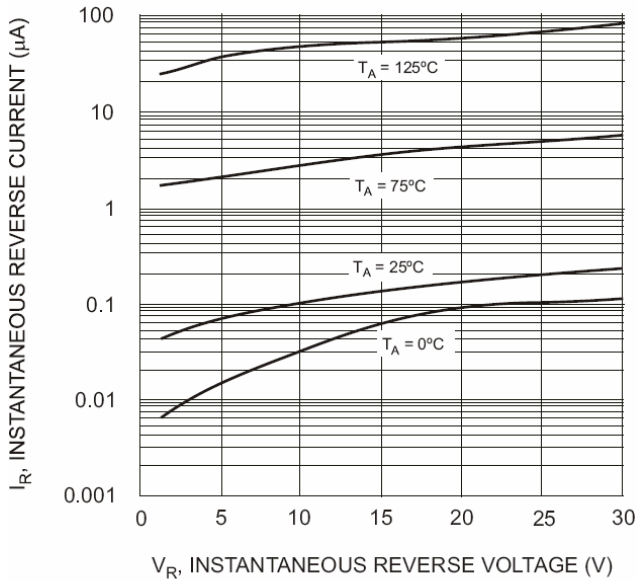


Fig. 3 Typical Reverse Characteristics

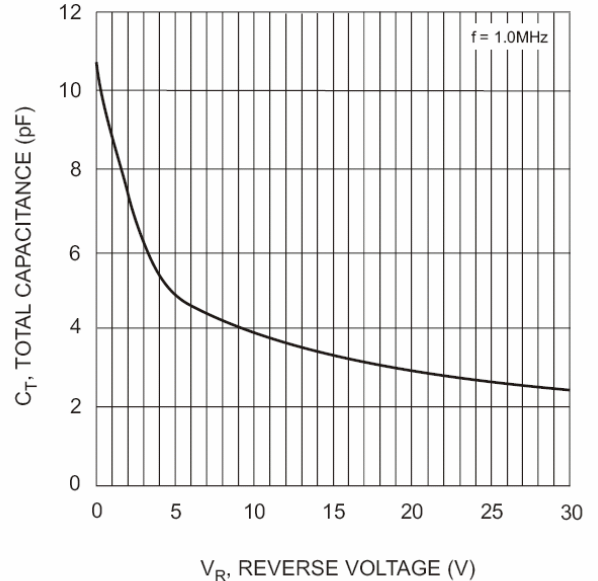


Fig. 4 Typical Capacitance vs. Reverse Voltage